

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 06-177381

(43)Date of publication of application : 24.06.1994

(51)Int.Cl.
H01L 29/784
G02F 1/136
H01L 21/306
H01L 21/318
// H01L 21/3205

(21)Application number : 04-323510

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(22)Date of filing : 03.12.1992

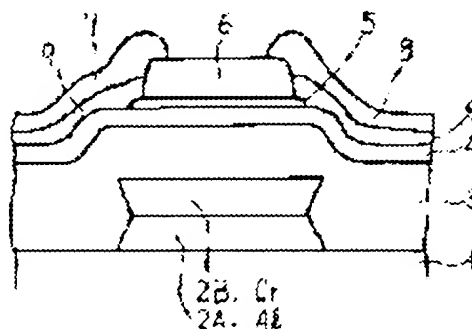
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(54) MATRIX OF THIN FILM TRANSISTOR AND ITS MANUFACTURE

(57)Abstract:

PURPOSE: To suppress the destruction and characteristic change of a thin film transistor (TFT) by static electricity so as to eliminate wrong display by forming a gate having an acute upper edge in its cross section on a substrate.

CONSTITUTION: A gate insulating film having a two-layer structure composed of an alumina film 3 formed by the ALD method and silicon nitride film 4 formed by the P-CVD method is formed on gate electrodes 2A and 2B and gate bus line formed on an NATO glass substrate 1 formed as a transparent insulating substrate. Then, after forming a working semiconductor layer 5 composed of an a-Si film 5, protective film 6 composed of a silicon nitride film, contact layer 9 composed of an m+ a-Si film 9 by using the P-CVD method, etc., a source and drain electrodes 7 and 8 and drain bus line are formed as the matrix of a TFT. Therefore, the destruction and characteristic change of the TFT caused by static electricity can be suppressed and the occurrence of wrong display can be reduced, since the withstand voltage characteristic of the gate insulating film is improved.



LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]